



# SPN138N08

## N-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPN138N08 is the N-Channel enhancement mode power field effect transistor which is produced using high cell density DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suitable for synchronous rectifier application, Motor control power management and other Power Tool circuits. It has been optimized for low gate charge, low  $R_{DS(ON)}$  and fast switching speed.

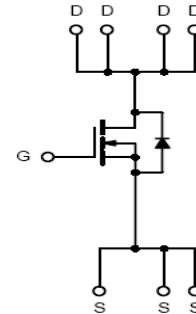
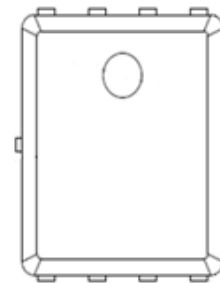
### FEATURES

- ◆ 80V/138A,  $R_{DS(ON)}=3.6m\Omega@V_{GS}=10V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ PPAK5x6-8L package design

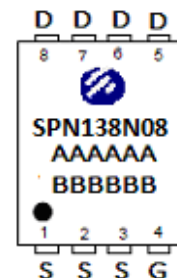
### APPLICATIONS

- DC/DC Converter
- Load Switch
- SMPS Secondary Side Synchronous Rectifier
- Power Tool
- Motor Control

### PIN CONFIGURATION (PPAK5x6-8L)



### PART MARKING



A : Lot Code  
 B : Date Code  
 (YY/MM/DD)



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### PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPN138N08DN8RGB	PPAK5x6-8L	SPN138N08

※ SPN138N08DN8RGB : 13" Tape Reel ; Pb – Free ; Halogen – Free

### ABSOLUTE MAXIMUM RATINGS

( $T_A=25^{\circ}\text{C}$  Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	$V_{DSS}$	80	V	
Gate –Source Voltage	$V_{GSS}$	$\pm 20$	V	
Continuous Drain Current(Silicon Limited)	$I_D$	$T_C=25^{\circ}\text{C}$	138	A
		$T_C=100^{\circ}\text{C}$	88	
Pulsed Drain Current	$I_{DM}$	400	A	
Avalanche Energy with Single Pulse ( $T_C=25^{\circ}\text{C}$ , $L = 0.4\text{mH}$ )	$E_{AS}$	320	mJ	
Power Dissipation	$P_D$	$T_C=25^{\circ}\text{C}$	83	W
		$T_A=70^{\circ}\text{C}$	1.6	
Operating Junction Temperature	$T_J$	-55/150	$^{\circ}\text{C}$	
Storage Temperature Range	$T_{STG}$	-55/150	$^{\circ}\text{C}$	
Thermal Resistance-Junction to Case	$R_{\theta JC}$	1.5	$^{\circ}\text{C}/\text{W}$	



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### ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

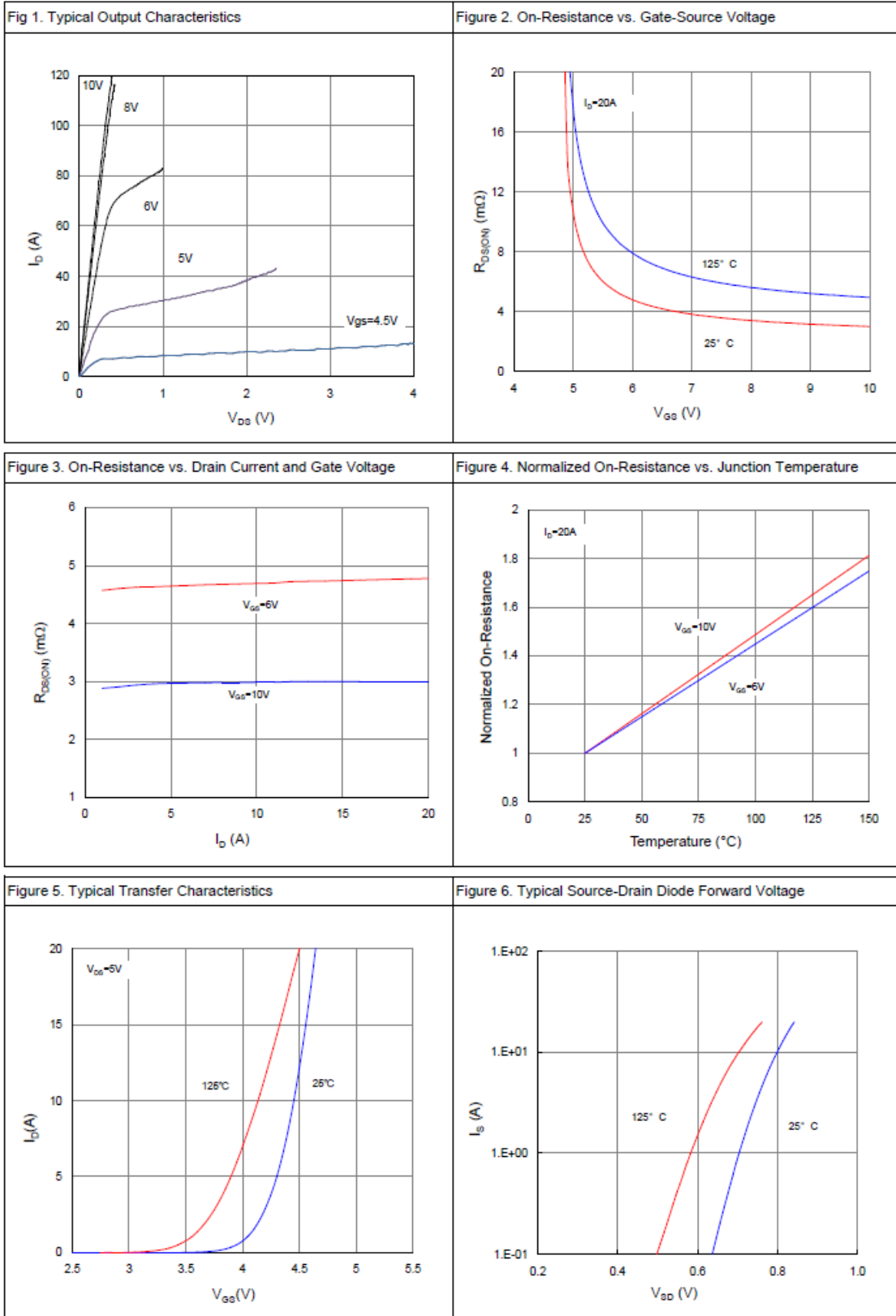
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=80V, V_{GS}=0V$ $T_J=25^\circ C$			1	uA
		$V_{DS}=80V, V_{GS}=0V$ $T_J=100^\circ C$			100	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		3.0	3.5	m $\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS}=5V, I_D=20A$		64		S
Gate Resistance	$R_G$	$V_{GS}=0V, V_{DS}=Open,$ $f=1MHz$		1.2		$\Omega$
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=40V, V_{GS}=10V$ $I_D=20A$		68		nC
Gate-Source Charge	$Q_{gs}$			13		
Gate-Drain Charge	$Q_{gd}$			17		
Input Capacitance	$C_{iss}$	$V_{DS}=40V, V_{GS}=0V$ $f=1MHz$		4350		pF
Output Capacitance	$C_{oss}$			704		
Reverse Transfer Capacitance	$C_{rss}$			28		
Turn-On Time	$t_{d(on)}$	$V_{DD}=40V, I_D=20A,$ $V_{GS}=10V, R_G=10\Omega$		16		nS
	$t_r$			12		
Turn-Off Time	$t_{d(off)}$			50		
	$t_f$			19		
<b>Reverse Recovery</b>						
Diode Forward Voltage	$V_{SD}$	$I_F=20A, V_{GS}=0V$		0.9	1.2	V
Reverse Recovery Time	$T_{rr}$	$V_R=40V, I_F=20A,$		50		nS
Reverse Recovery Charge	$Q_{rr}$	$dI_F/dt=100A/\mu S$		61		nC



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### TYPICAL CHARACTERISTICS

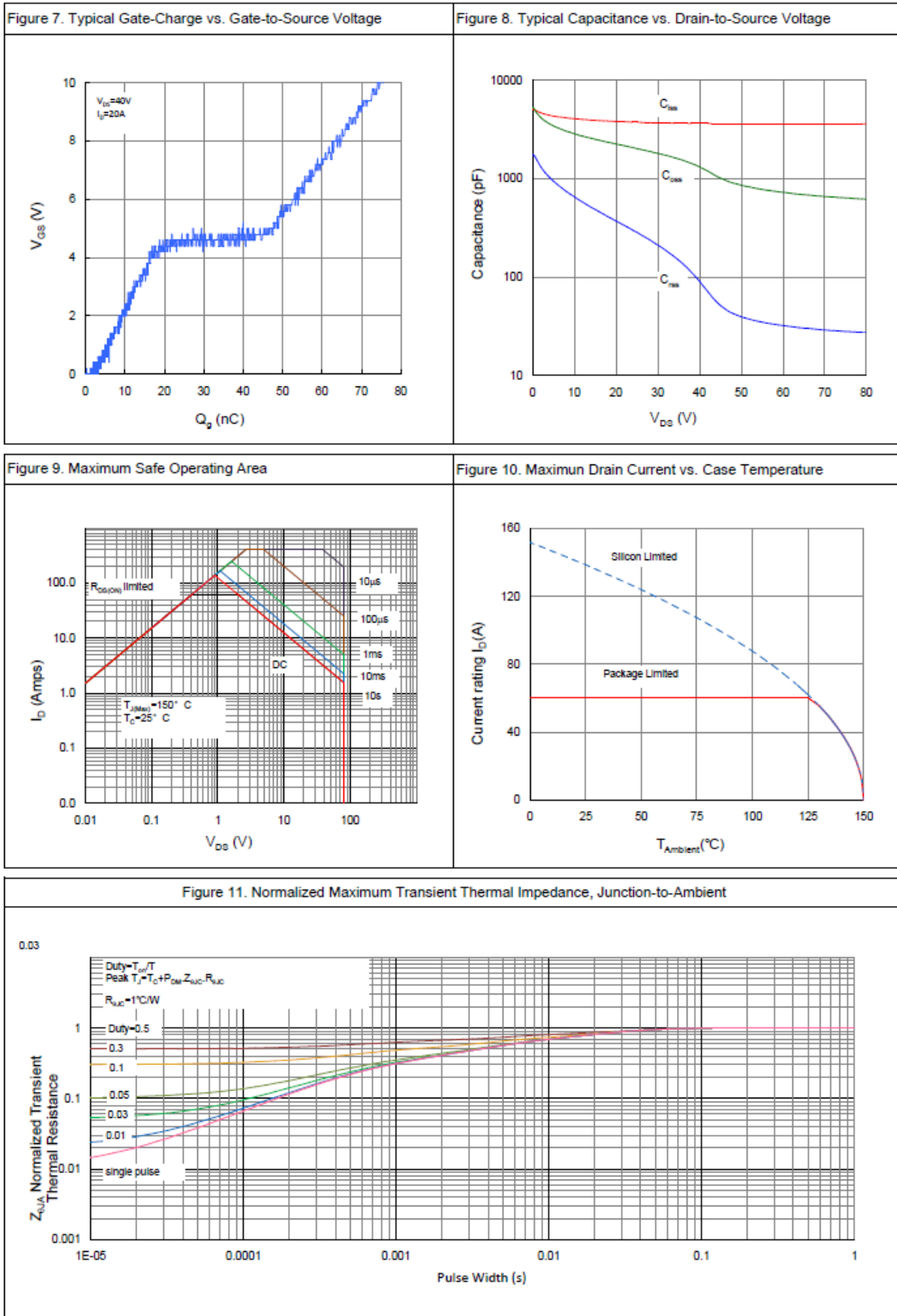




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### TYPICAL CHARACTERISTICS





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